

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known Application Number NEW- 10/736617 Filing Date December 12 2003 First Named Inventor Kristy A. Campbell Art Unit N/A 2824B Examiner Name Not Yet Assigned V. Yeusikov Attorney Docket Number M4065.0698/P698-A	
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Examiner Initials*	Cite No.†	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No.†	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T²
		Country Code³	Number⁴-Kind Code⁵ (if known)				
VY	BA	WO	97/48032	12/18/1997	Kozicki et al.		
VY	BB	WO	95/28914	06/10/1999	Kozicki et al.		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. †Applicant's unique citation designation number (optional). ‡See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 601.04. §Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ¶For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. **Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ***Applicant is to place a check mark here if English language Translation is attached.

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		Filing Date	December 12, 2003
		First Named Inventor	Kristy A. Campbell
		Art Unit	N/A 2829
		Examiner Name	Not Yet Assigned Yevsi Kov
		Attorney Docket Number	M4065.0698/P698-A
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			Filing Date	December 18, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	MA-2329	
			Examiner Name	Not Yet Assigned - Yevsi Kov	
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		Art Unit	N/A 2829		
		Examiner Name	Not Yet Assigned Ye vsi Ko ✓		
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		Application Number	NEW- 10734617
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		First Named Inventor	Kristy A. Campbell
		Art Unit	N/A 2824
		Examiner Name	Not Yet Assigned Yevsi Kov
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	NEW- 15736617
		Filing Date	December 22, 2003
		First Named Inventor	Kristy A. Campbell
		Art Unit	N/A 2829
		Examiner Name	Not Yet Assigned - Yevsi Kov
		Attorney Docket Number	M4065.0698/P698-A
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Substitute for form 1449A/B/PTO <h2 style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center;">(Use as many sheets as necessary)</p>		Complete If Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>NEW-101736619</td> </tr> <tr> <td>Filing Date</td> <td>December 12, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Kristy A. Campbell</td> </tr> <tr> <td>Art Unit</td> <td>N/A 2829</td> </tr> <tr> <td>Examiner Name</td> <td>Not Yet Assigned Yersikov</td> </tr> <tr> <td>Attorney Docket Number</td> <td>M4065.0698/P698-A</td> </tr> </table>		Application Number	NEW-101736619	Filing Date	December 12, 2003	First Named Inventor	Kristy A. Campbell	Art Unit	N/A 2829	Examiner Name	Not Yet Assigned Yersikov	Attorney Docket Number	M4065.0698/P698-A
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Sheet	8	of	8												

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				Application Number	10/736,617
				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2825 2829 B
Examiner Name	R. Rocchegiani	VYEVSIK			
Attorney Docket Number	M4065.0698/P698-A				
Sheet	1	of	5		

U. S. PATENT DOCUMENTS					
Exami ner Initials	Cite No.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	**AT1	3,983,542	11/1976	Ovshinsky	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/736,617
				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2825 9
				Examiner Name	R. Reehogiani Yevstikov
Sheet	2	of	5	Attorney Docket Number	M4065.0698/P698-A

V4	**AU1	3,988,720	10/1976	Ovshinsky	
4	**AV1	4,177,474	12/1979	Ovshinsky	
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				Application Number	10/736,617
				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2825 9
				Examiner Name	R. Reechegant-Yersikov
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✓	**AN5	6,420,725	7/16/2002	Harshfield	

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				Art Unit	2829
				Examiner Name	R. Rocchegiani Yevsikov
Sheet	4	of	5	Attorney Docket Number	M4065.0698/P698-A

✓	**AO5	6,423,628	7/2002	Li et al.	
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				Application Number	10/736,617
				Filing Date	December 17, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2828 9
				Examiner Name	R. Rocchegiani Yevsi KOV
Sheet	5	of	5	Attorney Docket Number	M4065.0698/P698-A

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.†	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T*
		Country Code‡	Number⁴-Kind Code⁵ (if known)				
✓	**BA	JP	5-6126916	10/19981	Akira et al.		
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Examiner Signature	V. Yevsi KOV	Date Considered	03/01/05
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